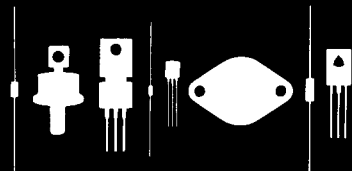


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145 Adams Avenue  
Hauppauge, New York 11788



2N1479  
2N1480  
2N1481  
2N1482

NPN SILICON TRANSISTOR

JEDEC TO-39 CASE

## DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N1479 series types are silicon NPN transistors manufactured by the epitaxial planar process, mounted in a hermetically sealed metal case designed for switching and amplifier applications.

MAXIMUM RATINGS ( $T_C=25^\circ\text{C}$  unless otherwise noted)

	SYMBOL	2N1479 2N1481	2N1480 2N1482	UNIT
Collector-Base Voltage	V <sub>CB0</sub>	60	100	V
Collector-Emitter Voltage	V <sub>CEV</sub>	60	100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	55	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	6.0	V
Collector Current	I <sub>C</sub>	1.5	1.5	A
Base Current	I <sub>B</sub>	1.0	1.0	A
Power Dissipation	P <sub>D</sub>	5.0	5.0	W
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>STG</sub>	-65 TO +200		°C
Thermal Resistance	θ <sub>JC</sub>	35		°C/W

ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N1479		2N1480		2N1481		2N1482		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
I <sub>CB0</sub>	V <sub>CB</sub> =30V		10		10		10		10	μA
I <sub>CB0</sub>	V <sub>CB</sub> =30V, T <sub>C</sub> =150°C		500		500		500		500	μA
I <sub>EBO</sub>	V <sub>EB</sub> =6.0V		10		10		10		10	μA
V <sub>CEV</sub>	V <sub>EB</sub> =1.5V, I <sub>C</sub> =0.25mA	60		100		60		100		V
V <sub>CEO</sub>	I <sub>C</sub> =50mA	40		55		40		55		V
V <sub>CE</sub> (SAT)	I <sub>C</sub> =200mA, I <sub>B</sub> =10mA		-		-		1.4		1.4	V
V <sub>CE</sub> (SAT)	I <sub>C</sub> =200mA, I <sub>B</sub> =20mA		1.4		1.4		-		-	V
V <sub>BE</sub> (ON)	V <sub>CE</sub> =4.0V, I <sub>C</sub> =200mA		3.0		3.0		3.0		3.0	V
h <sub>FE</sub>	V <sub>CE</sub> =4.0V, I <sub>C</sub> =200mA	20	60	20	60	35	100	35	100	
h <sub>fe</sub>	V <sub>CE</sub> =4.0V, I <sub>C</sub> =5.0mA		50 TYP		50 TYP		50 TYP		50 TYP	
t <sub>ON</sub>	I <sub>C</sub> =200mA, I <sub>B1</sub> =20mA, I <sub>B2</sub> =85mA		1.2 TYP		1.2 TYP		1.2 TYP		1.2 TYP	μs
t <sub>OFF</sub>	I <sub>C</sub> =200mA, I <sub>B1</sub> =20mA, I <sub>B2</sub> =85mA		1.6 TYP		1.6 TYP		1.6 TYP		1.6 TYP	μs
C <sub>ob</sub>	V <sub>CB</sub> =40V		150 TYP		150 TYP		150 TYP		150 TYP	pF
f <sub>αB</sub>	V <sub>CB</sub> =28V, I <sub>C</sub> =5.0mA		1.5 TYP		1.5 TYP		1.5 TYP		1.5 TYP	MHz

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